## Product Specifications <br> J uly 1997 <br> (1 of 4)

## Features

- High Gain
$\square+30 \mathrm{dBm}$ Power Output
$\square$ Proprietary Power FET Process
$\square>40 \%$ Linear Power Added Efficiency
$\square$ Surface Mount SO-8 Power Package


## Applications

## $\square$ ISM Band Base Stations and Terminals

RF ID/POS Base Stations
$\square$ Wireless Local Loop

## Description

The CFK2062-P5 is a high-gain FET intended for driver amplifier applications in high-power systems, and output stage usage in medium power applications at power levels up to +30 dBm . The device is easily matched and provides excellent

Specifications $\left(\mathrm{TA}=25^{\circ} \mathrm{C}\right)$ The following specifications are guaranteed at room temperature in Celeritek test fixture at 2.45 GHz .

| Parameters | Conditions | Min | Typ | Max | Units |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{d}}=8 \mathrm{~V}, \mathrm{I}_{\mathrm{d}}=400 \mathrm{~mA}$ (Quiescent) |  |  |  |  |  |
| $\mathrm{P}_{\text {-1dB }}$ |  | 30.0 | 31.0 | - | dBm |
| SSG |  | 12.0 | 13.0 | - | dB |
| 3rd Order <br> Products $\qquad$ |  | - | 30 | - | dBc |
| Efficiency | @ P1dB | - | 40 | - | \% |
| $\mathrm{V}_{\mathrm{d}}=\mathbf{5 V}, \mathrm{I}_{\mathrm{d}}=\mathbf{6 0 0} \mathrm{mA}$ (Quiescent) |  |  |  |  |  |
| $\mathrm{P}_{\text {-1dB }}$ |  | - | 30.5 | - | dBm |
| SSG |  | - | 12.0 | - | dB |


| Parameters | Conditions | Min | Typ | Max | Units |
| :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathbf{g}_{\mathbf{m}}$ | Vds $=2.0 \mathrm{~V}, \mathrm{Vgs}=0 \mathrm{~V}$ | - | 650 | - | mS |
| $\mathbf{I}_{\mathbf{d s s}}$ | Vds $=2.0 \mathrm{~V}, \mathrm{Vgs}=0 \mathrm{~V}$ | - | 1.4 | - | A |
| $\mathbf{V}_{\mathbf{p}}$ | Vds $=3.0 \mathrm{~V}$, Ids $=25 \mathrm{~mA}$ | - | -1.8 |  | Volts |
| $\mathbf{B V}_{\mathbf{G D}}$ | Igd $=2.5 \mathrm{~mA}$ | 15 | 17 | - | Volts |
| $\Theta_{\mathbf{J L}}{ }^{(2)}$ | $@ 150^{\circ} \mathrm{C}$ TCH | - | 12 | - | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Absolute Maximum Ratings

| Parameter | Symbol | Rating |
| :--- | :---: | :---: |
| Drain-Source Voltage | $\mathrm{V}_{\mathrm{DS}}$ | $10 \mathrm{~V}^{(3)}$ |
| Gate-Source Voltage | $\mathrm{V}_{\mathrm{GS}}$ | -5 V |
| Drain Current | $\mathrm{I}_{\mathrm{DS}}$ | Idss |
| Continuous Dissipation | $\mathrm{P}_{\mathrm{T}}$ | 6 W |
| Channel Temperature | $\mathrm{T}_{\mathrm{CH}}$ | $175^{\circ} \mathrm{C}$ |
| Storage Temperature | $\mathrm{T}_{\text {STG }}$ | $-65^{\circ} \mathrm{C}$ to $+175^{\circ} \mathrm{C}$ |

## 2.3 to 2.5 GHz +30 dBm Power GaAs FET

## Package Diagram


linearity at 1 Watt. Manufactured in Celeritek's proprietary power FET process, this device is assembled in an industry standard surface mount SO-8 power package that is compatible with high volume, automated board assembly techniques.

## SO-8 Power Package Physical Dimensions




| DIMENSION | MINIMUM | NOMINAL | MAXIMUM |
| :---: | :---: | :---: | :---: |
| A |  | $.086[2.184]$ | $.100[2.540]$ |
| A1 | $.005[.1270]$ | $.008[.2032]$ | $.011[.2794]$ |
| b | $.017[.4318]$ | $.020[.5080]$ | $.023[.5842]$ |
| c | $.007[.1778]$ | $.008[2032]$ | $.009[.2286]$ |
| D | $.195[4.953]$ | $.200[5.080]$ | $.205[5.207]$ |
| E | $.135[3.429]$ | $.140[3.556]$ | $.145[3.683]$ |
| E 1 | $.155[3.937]$ | $.160[4.064]$ | $.165[4.191]$ |
| e |  | $.050[1.270]$ |  |
| L | $.020[.5080]$ |  | $.040[1.016]$ |
| $\mathrm{L1}$ | $.055[1.397]$ | $.065[1.651]$ | $.075[1.905]$ |
| $\propto$ | 0 |  | 8 |

DIMENSIONS IN INCHES [MILIMETERS]

## Notes:

1. Sum to two tones with 1 MHz spacing $=25 \mathrm{dBm}$.
2. See thermal considerations information on page 4.
3. Maximum potential difference across the device $(\mathrm{Vd}+\mathrm{Vg})$ cannot exceed 12 V .

Typical Scattering Parameters $\quad\left(\mathrm{TA}=25^{\circ} \mathrm{C}\right.$, $\mathrm{Vds}=5 \mathrm{~V}$, Ids $\left.=\mathbf{6 0 0} \mathrm{mA}\right)$

| $\begin{aligned} & \text { Frequency } \\ & \text { (GHz) } \end{aligned}$ | $\mathrm{S}_{11}$ |  | $\mathrm{S}_{21}$ |  | $\mathrm{S}_{12}$ |  | $\mathrm{S}_{22}$ |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Mag | Ang | Mag | Ang | Mag | Ang | Mag | Ang |
| 0.6 | 0.927 | -129.75 | 8.7 | 102.7 | 0.024 | 21.95 | 0.576 | -178.45 |
| 1.0 | 0.914 | -154.69 | 5.449 | 84.82 | 0.025 | 8.72 | 0.6 | 175.04 |
| 1.8 | 0.889 | -174.42 | 3.768 | 61.32 | 0.033 | -5.24 | 0.53 | 163.11 |
| 1.9 | 0.866 | -178.39 | 3.693 | 57.12 | 0.035 | -8.52 | 0.52 | 159.17 |
| 2.0 | 0.883 | 177.09 | 3.605 | 52.62 | 0.05 | -10.6 | 0.512 | 154.61 |
| 2.1 | 0.78 | 171.92 | 3.504 | 48.01 | 0.035 | -14.75 | 0.508 | 149.35 |
| 2.2 | 0.879 | 166.48 | 3.386 | 42.82 | 0.036 | -18.18 | 0.509 | 143.77 |
| 2.3 | 0.88 | 160.6 | 3.243 | 37.96 | 0.036 | -22.89 | 0.515 | 137.96 |
| 2.4 | 0.884 | 154.86 | 3.09 | 32.93 | 0.035 | -26.59 | 0.528 | 132.84 |
| 2.5 | 0.887 | 150.54 | 2.944 | 28.96 | 0.035 | -30.13 | 0.539 | 128.94 |
| 2.6 | 0.891 | 145.9 | 2.757 | 24.85 | 0.035 | -32.91 | 0.555 | 124.99 |
| 2.7 | 0.899 | 141.82 | 2.57 | 20.93 | 0.035 | -37.19 | 0.574 | 122.00 |
| 3.0 | 0.917 | 135.01 | 2.081 | 13.19 | 0.03 | -41.27 | 0.623 | 118.42 |
| 3.5 | 0.932 | 137.14 | 1.635 | 8.18 | 0.028 | -41.69 | 0.643 | 124.18 |
| 4.0 | 0.913 | 143.42 | 1.641 | 3.36 | 0.032 | -41.15 | 0.557 | 131.38 |

$\left(\mathbf{T A}=25^{\circ} \mathrm{C}, \mathrm{Vds}=8 \mathrm{~V}, \mathrm{Ids}=400 \mathrm{~mA}\right)$

| 0.6 | 0.91 | -131.25 | 9.129 | 100.5 | 0.026 | 17.07 | 0.521 | -174.04 |
| :--- | :--- | :--- | :--- | ---: | :--- | ---: | :--- | :--- |
| 1.0 | 0.904 | -155.33 | 5.68 | 82.61 | 0.027 | 6.34 | 0.548 | 178.8 |
| 1.8 | 0.883 | -174.77 | 3.86 | 58.87 | 0.034 | -7.72 | 0.483 | 168.5 |
| 1.9 | 0.88 | -178.6 | 3.783 | 54.83 | 0.034 | -9.68 | 0.472 | 164.9 |
| 2.0 | 0.877 | 176.74 | 3.696 | 50.36 | 0.035 | -13.77 | 0.463 | 160.21 |
| 2.1 | 0.873 | 171.86 | 3.589 | 45.5 | 0.036 | -16.17 | 0.458 | 154.9 |
| 2.2 | 0.874 | 166.29 | 3.46 | 40.56 | 0.037 | -21.9 | 0.458 | 149.35 |
| 2.3 | 0.876 | 160.6 | 3.324 | 35.55 | 0.036 | -26.41 | 0.463 | 143.16 |
| 2.4 | 0.878 | 154.94 | 3.159 | 30.56 | 0.036 | -29.59 | 0.475 | 137.57 |
| 2.5 | 0.882 | 150.43 | 3.014 | 26.66 | 0.036 | -31.65 | 0.486 | 133.49 |
| 2.6 | 0.888 | 145.65 | 2.872 | 22.43 | 0.035 | -33.01 | 0.504 | 129.21 |
| 2.7 | 0.893 | 141.74 | 2.643 | 18.41 | 0.035 | -39.11 | 0.524 | 125.87 |
| 3.0 | 0.915 | 135.06 | 2.136 | 10.26 | 0.031 | -46.6 | 0.579 | 121.99 |
| 3.5 | 0.93 | 137.37 | 1.662 | 4.59 | 0.027 | -43.86 | 0.611 | 128.44 |
| 4.0 | 0.912 | 143.75 | 1.642 | -0.35 | 0.031 | -43.95 | 0.541 | 137.64 |

RF Match Data shown in the performance graphs was taken in the test circuit shown at right. Layout is important for proper operation. Phase length of input and output $50 \Omega$ line varies as a function of exact desired frequency of operation. Output shunt inductor effects output performance. Celeritek recommends the use of a high impedance printed inductor Lambda/4 in length. Please contact the factory for an evaluation board and/or more detailed application support.


## Typical Performance

Power Output \& Power Added Efficiency vs Power Input $2.45 \mathrm{GHz}, \mathrm{V}_{\mathrm{DS}}=8 \mathrm{~V}, \mathrm{I}_{\mathrm{DS}}=400 \mathrm{~mA}$


Power Output and Gain vs Frequency


Power Output and Gain vs Voltage @ 2.45 GHz


Power Output \& Power Added Efficiency vs Power Input


Power Output and Gain vs Frequency


Power Output and Gain vs Voltage @ 2.45 GHz
$\mathrm{I}_{\mathrm{DS}}=600 \mathrm{~mA}$


## Thermal Considerations

The data shown was taken on a 31 mil thick FR-4 board with 1 ounce copper on both sides. The board was mounted to a baseplate with 3 screws as shown. The screws bring the top side copper temperature to the same value as the baseplate. The thermal resistance to the indicated reference lead, $\Theta_{\mathrm{JL}}$, is $12^{\circ} \mathrm{C} / \mathrm{W}$. The thermal resistance to the reference screw is $14^{\circ} \mathrm{C} / \mathrm{W}$.

1. Use 1 or 2 ounce copper if possible.
2. Solder all eight leads of the CFK2062-P5 package to the appropriate electrical connection.
3. Solder the copper pad on the backside of the CFK2062-P5 package to the ground plane.
4. Use a large ground pad area with many plated through-holes as shown.
5. If possible, use at least one screw no more than 0.2 inches from the CFK2062-P5 package to provide a low thermal resistance path to the baseplate of the package.


BOARD LAYOUT


## Ordering Information

The CFK2062-P5 power stage is available in a SO-8 surface mount package. Devices are available in tape and reel. Ordering part numbers are listed.

Part Number for Ordering
CFK2062-P5
CFK2062-P5-000T

Function
2.3-2.5 GHz Power Stage
2.3-2.5 GHz Power Stage

## Package

SO-8 surface mount power package
SO-8 surface mount power package in tape and reel

